

1449A/PTO Rev. 10/95		U.S. Department of Commerce Patent and Trademark Office		Complete If Known	
LIST OF PRIOR ART CITED BY APPLICANT (use as many sheets as necessary)				Application Number	10/625 015
				Filing Date	07-22-03
				First Named Inventor	Jer-shen Maa
				Group Art Unit	2813
				Examiner Name	NGUYEN
Sheet	1	of	2	Attorney Docket No.	SLA.0749

U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No. ¹	U.S. Patent Document Kind Number	Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear
TN		6,562,703 B1		Maa et al.	05-13-03	
TN		6,464,780 B1		Manti et al.	10-15-02	
TN		6,486,008 B1		Lee	11-26-02	
TN		5,877,070		Goesele et al.	03-02-99	

FOREIGN PATENT DOCUMENTS								
Examiner Initials	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document..	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear	T ⁶
		Office ³ Code ²	Number ⁴	Kind				

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, country where published, source.	T ²
TN		G.F. CEROFOLINI et al., <i>Hydrogen-related Complexes as the Stressing Species in High-fluence, Hydrogen-implanted, Single-crystal Silicon</i> , Physical Review B, vol. 46, p. 2061 (1992)	
TN		DEEPAK K. NAYAK et al., <i>High-Mobility Strained-Si PMOSFETs</i> , IEEE Transactions on Electron Devices, Vol. 43, 1709 (1996)	
TN		ADITYA AGARWAL et al., <i>Efficient Production of Silicon-on-Insulator Films by Co-implantation of He⁺ with H⁺</i> , Proceedings of the 1997 IEEE International SOI Conference, p. 44, (1997).	

Examiner Signature	T. NGUYEN	Date Considered	5/12/04
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TN		M.K. WELDON <i>et al.</i> , <i>On the Mechanism of the Hydrogen-Induced Exfoliation of Silicon</i> , J. Vac. Sci. Technol. B. 15, 1065, (1997)	
TN		S. MANTL <i>et al.</i> , <i>Strain Relaxation of Epitaxial SiGe Layers on Si(100) Improved by Hydrogen Implantation</i> , Nuclear Instruments and Methods in Physics Research B 147, 29, (1999)	
TN		H. TRINKAUS <i>et al.</i> , <i>Strain Relaxation Mechanism for Hydrogen-Implanted Si_{1-x}Ge_x/Si(100) Heterostructures</i> , Appl. Phys. Lett., 76, 3552, (2000)	
TN		K. RIM <i>et al.</i> , <i>Strained Si NMOSFETs for High Performance CMOS Technology</i> , 2001 Symposium on VLSI Technology Digest of Technical Papers, p. 59, (IEEE 2001)	
TN		JASON T.S. LIN <i>et al.</i> , <i>Nova Cut™ Process: Fabrication of Silicon-on Insulator Materials</i> , 2002 IEEE International SOI Conference, Williamsburg, Virginia, (2002)	
TN		M. LUYSBERG <i>et al.</i> , <i>Effect of helium ion implantation and annealing on the relaxation behavior of pseudomorphic Si_{1-x}Ge_x Buffer Layers on Si(100) substrates</i> , Journal of Applied Physics, Vol. 92, No. 8 (2002)	

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